

高速差分线路接收器

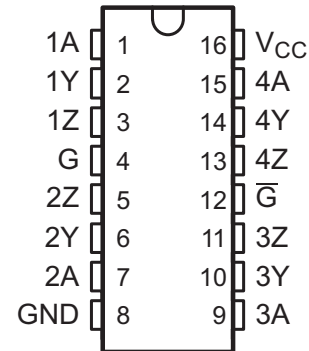
 查询样品: [SN65LVDS31-EP](#)

特性

- 满足或者超过 **ANSI TIA/EIA-644** 标准
- 具有 **350 mV** 的典型输出电压和 **100-Ω** 负载的低电压差分信号传输
- 典型输出电压上升和下降次数为 **500 ps (400 Mbps时)**
- 典型传播时延 **1.7 ns**
- **3.3-V** 单电源供电下运行
- **200 MHz**时, 每个驱动器功率耗散典型值 **25 mW**
- 当被禁止或者 $V_{CC} = 0$ 时, 驱动器在高阻抗
- 总线终端 **ESD** 保护超过 **8 kV**
- 低电压 **TTL (LVTTTL)** 逻辑输入电平
- 与 **AM26LS31**, **MC3487**, 和 **μA9638** 引脚兼容
- 用于有冗余要求的空间和高可靠性应用的冷备份

支持国防、航天和医疗应用

- 受控基线
- 一个组装/测试场所
- 一个制造场所
- 在军用温度范围内 (**-55°C/125°C**) 工作
- 产品生命周期有所延长
- 拓展的产品改变通知
- 产品可追溯性

**D PACKAGE
(TOP VIEW)**


说明

SN65LVDS31 是一款差分线路驱动器, 此差分驱动器具有低电压差分信号传输 (LVDS) 的电气特性。此项信号传输技术降低了 5-V 差分标准电平的输出电压电平 (例如 TIA/EIA-422B) 以减少功耗, 增加交换速度并允许一个 3.3 V 供电轨的操作。当被启用时, 此驱动器将向 100-Ω 负载传送一个大小为 247 mV 的最小差分输出电压。

这个设备和信号传输技术的目标应用是在点到点和多点间 (一个驱动器和多个接收器) 通过接近 100 Ω 的受控阻抗介质传输数据。传输介质可以是印刷电路板印制线、背板或者电缆。数据传输的最终速率和距离取决于介质的衰减特性和对环境的噪声耦合。

SN65LVDS31 器件工作温度范围 -55°C 至 125°C。



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



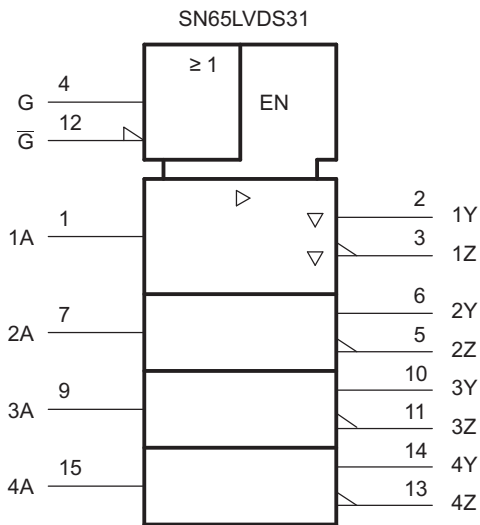
These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ORDERING INFORMATION⁽¹⁾

T _A	PACKAGE ⁽²⁾	ORDERABLE PART NUMBER	TOP-SIDE MARKING	VID NUMBER
-55°C to 125°C	SOIC-D	SN65LVDS31MDREP	LVDS31EP	V62/07627-01XE

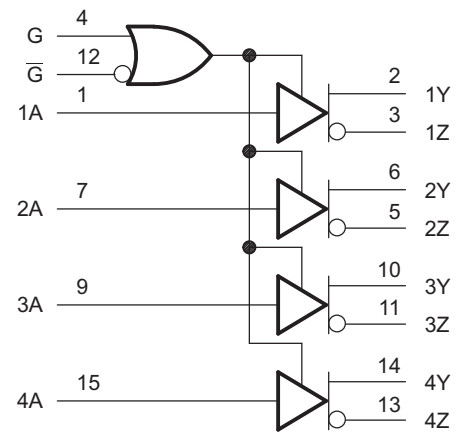
- (1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.
- (2) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

Logic Symbol



This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

SN65LVDS31 Logic Diagram (Positive Logic)



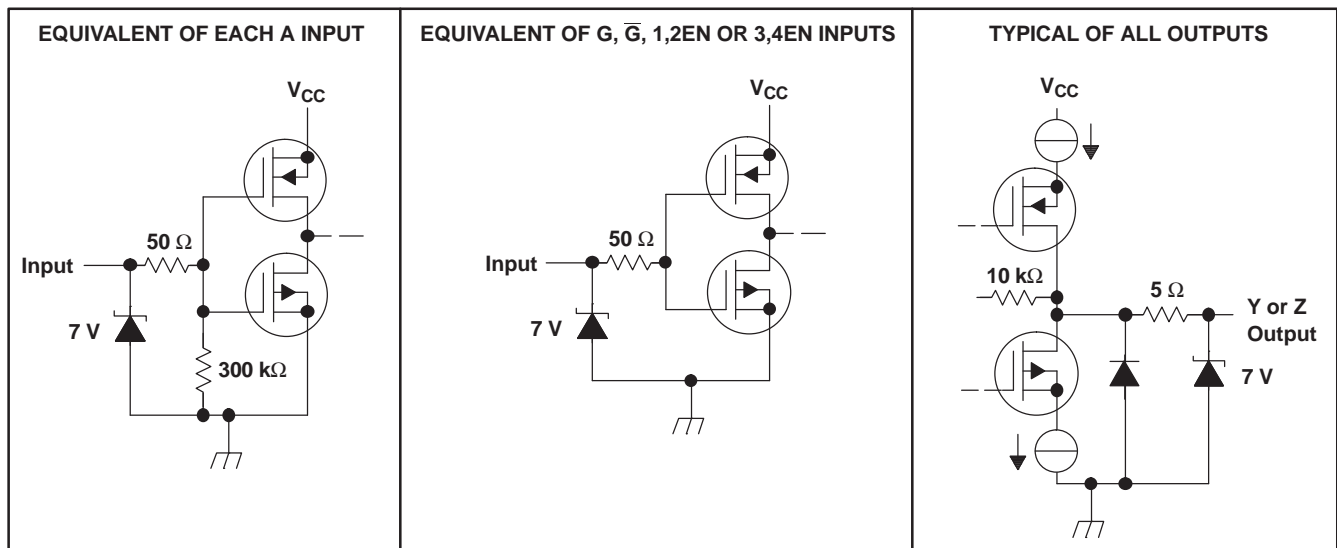
FUNCTION TABLE

Table 1. SN65LVDS31⁽¹⁾

INPUT A	ENABLES		OUTPUTS	
	G	\bar{G}	Y	Z
H	H	X	H	L
L	H	X	L	H
H	X	L	H	L
L	X	L	L	H
X	L	H	Z	Z
Open	H	X	L	H
Open	X	L	L	H

(1) H = high level, L = low level, X = irrelevant, Z = high impedance (off)

EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS



ABSOLUTE MAXIMUM RATINGS⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

	UNIT
V_{CC} Supply voltage range ⁽²⁾	–0.5 V to 4 V
V_I Input voltage range	–0.5 V to $V_{CC} + 0.5$ V
Continuous total power dissipation	See Dissipation Rating Table
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C
θ_{JA} Thermal resistance, junction-to-ambient	73°C/W
θ_{JC} Thermal resistance, junction-to-case	36.9°C/W
T_{stg} Storage temperature range	–65°C to 150°C

- (1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltages, except differential I/O bus voltages, are with respect to the network ground terminal.

DISSIPATION RATING TABLE

PACKAGE	$T_A \leq 25^\circ\text{C}$ POWER RATING	DERATING FACTOR ⁽¹⁾ ABOVE $T_A = 25^\circ\text{C}$	$T_A = 70^\circ\text{C}$ POWER RATING	$T_A = 85^\circ\text{C}$ POWER RATING	$T_A = 125^\circ\text{C}$ POWER RATING
D (16)	950 mW	7.6 mW/°C	608 mW	494 mW	190 mW

- (1) This is the inverse of the junction-to-ambient thermal resistance when board-mounted and with no air flow.

RECOMMENDED OPERATING CONDITIONS

	MIN	NOM	MAX	UNIT
V_{CC} Supply voltage	3	3.3	3.6	V
V_{IH} High-level input voltage	2			V
V_{IL} Low-level input voltage			0.8	V
T_A Operating free-air temperature	–55		125	°C

ELECTRICAL CHARACTERISTICS

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
V_{OD} Differential output voltage magnitude	$R_L = 100 \Omega$, See Figure 2	247	340	454	mV
ΔV_{OD} Change in differential output voltage magnitude between logic states	$R_L = 100 \Omega$, See Figure 2	–50		50	mV
$V_{OC(SS)}$ Steady-state common-mode output voltage	See Figure 3	1.125	1.2	1.375	V
$\Delta V_{OC(SS)}$ Change in steady-state common-mode output voltage between logic states	See Figure 3	–50		50	mV
$V_{OC(PP)}$ Peak-to-peak common-mode output voltage	See Figure 3		50		mV
I_{CC} Supply current	$V_I = 0.8$ V or 2 V, Enabled, No load		9	20	mA
	$V_I = 0.8$ or 2 V, $R_L = 100 \Omega$, Enabled		25	35	
	$V_I = 0$ or V_{CC} , Disabled		0.25	1	
I_{IH} High-level input current	$V_{IH} = 2$		4	20	μA
I_{IL} Low-level input current	$V_{IL} = 0.8$ V		0.1	10	μA
I_{OS} Short-circuit output current	$V_{O(Y)}$ or $V_{O(Z)} = 0$		–4	–24	mA
	$V_{OD} = 0$			± 12	
I_{OZ} High-impedance output current	$V_O = 0$ or 2.4 V			± 1	μA
$I_{O(OFF)}$ Power-off output current	$V_{CC} = 0$, $V_O = 2.4$ V			± 4	μA
C_i Input capacitance			3		pF

- (1) All typical values are at $T_A = 25^\circ\text{C}$ and with $V_{CC} = 3.3$ V.

SWITCHING CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
t_{PLH}	Propagation delay time, low-to-high-level output	$R_L = 100 \Omega$, $C_L = 10 \text{ pF}$, See Figure 2	0.5	1.4	4	ns
t_{PHL}	Propagation delay time, high-to-low-level output		1	1.7	4.5	ns
t_r	Differential output signal rise time (20% to 80%)		0.5			ns
t_f	Differential output signal fall time (80% to 20%)		0.5			ns
$t_{sk(p)}$	Pulse skew ($ t_{PHL} - t_{PLH} $)		0.3	0.6		ns
$t_{sk(o)}$	Channel-to-channel output skew ⁽²⁾		0.3	0.8		ns
t_{PZH}	Propagation delay time, high-impedance-to-high-level output	See Figure 4	5.4	17		ns
t_{PZL}	Propagation delay time, high-impedance-to-low-level output		2.5	17		ns
t_{PHZ}	Propagation delay time, high-level-to-high-impedance output		8.1	18		ns
t_{PLZ}	Propagation delay time, low-level-to-high-impedance output		7.3	17		ns

(1) All typical values are at $T_A = 25^\circ\text{C}$ and with $V_{CC} = 3.3 \text{ V}$.

(2) $t_{sk(o)}$ is the maximum delay time difference between drivers on the same device.

PARAMETER MEASUREMENT INFORMATION

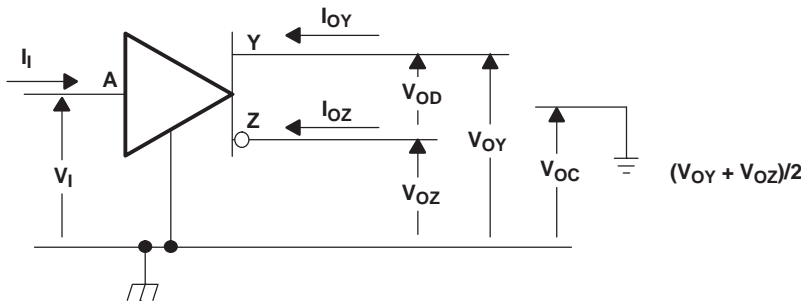
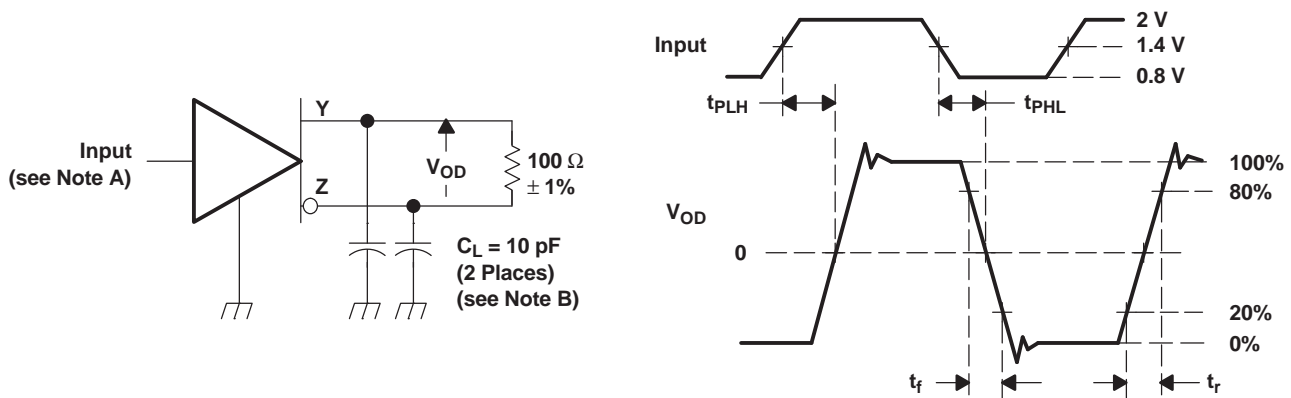


Figure 1. Voltage and Current Definitions

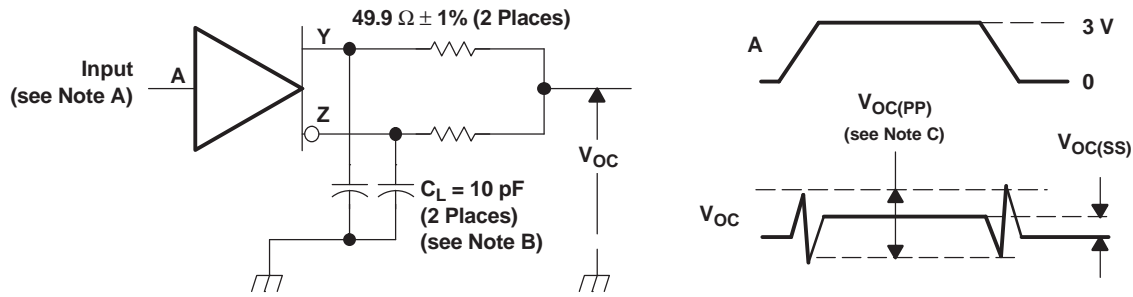


NOTES: A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \leq 1 \text{ ns}$, pulse repetition rate (PRR) = 50 Mpps, pulse width = $10 \pm 0.2 \text{ ns}$.

B. C_L includes instrumentation and fixture capacitance within 6 mm of the D.U.T.

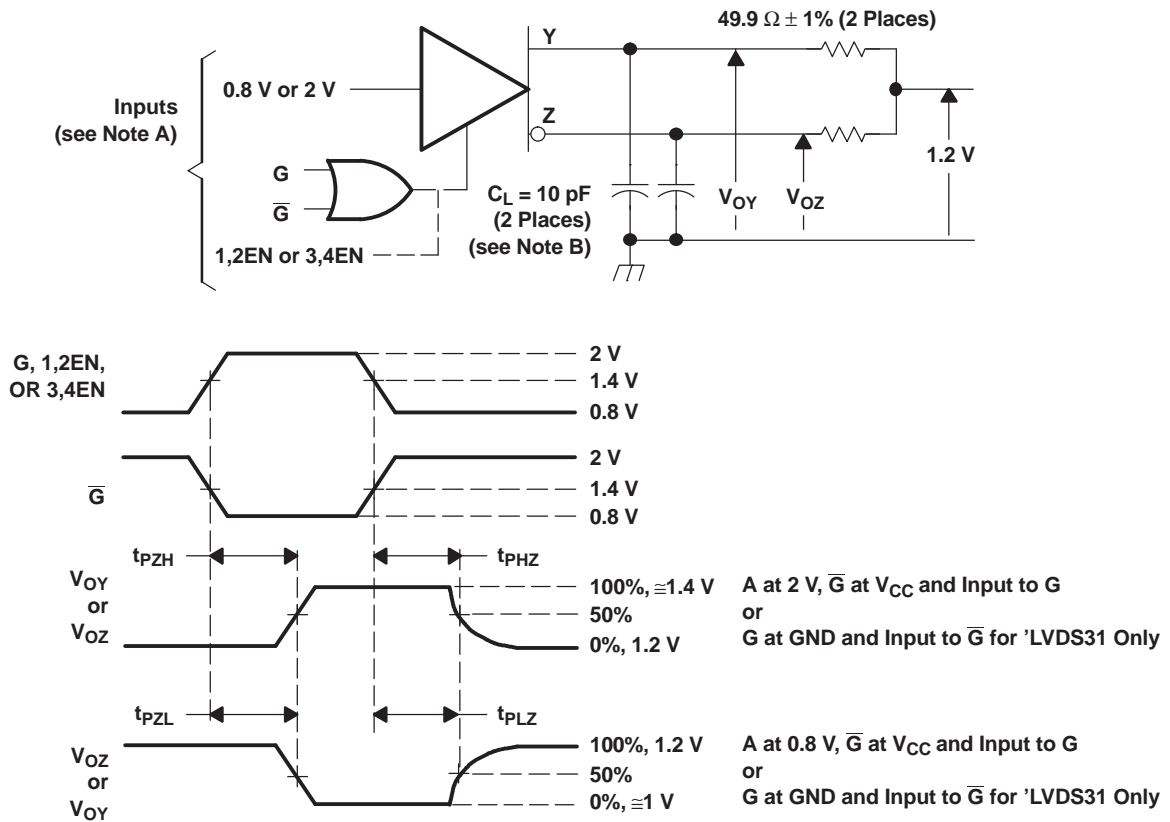
Figure 2. Test Circuit, Timing, and Voltage Definitions for the Differential Output Signal

PARAMETER MEASUREMENT INFORMATION (continued)



- NOTES: A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \leq 1$ ns, pulse repetition rate (PRR) = 50 Mpps, pulse width = 10 ± 0.2 ns.
 B. C_L includes instrumentation and fixture capacitance within 6 mm of the D.U.T.
 C. The measurement of $V_{OC(PP)}$ is made on test equipment with a -3 -dB bandwidth of at least 300 MHz.

Figure 3. Test Circuit and Definitions for the Driver Common-Mode Output Voltage



- NOTES: A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f < 1$ ns, pulse repetition rate (PRR) = 0.5 Mpps, pulse width = 500 ± 10 ns.
 B. C_L includes instrumentation and fixture capacitance within 6 mm of the D.U.T.

Figure 4. Enable-/Disable-Time Circuit and Definitions

TYPICAL CHARACTERISTICS

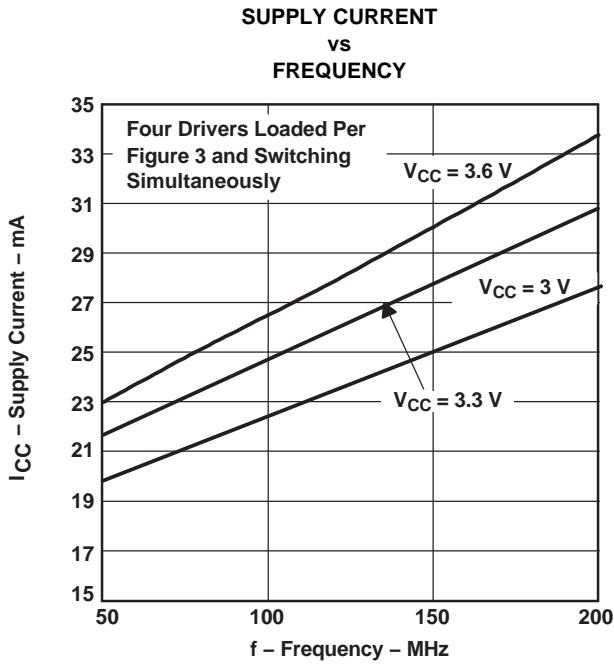


Figure 5.

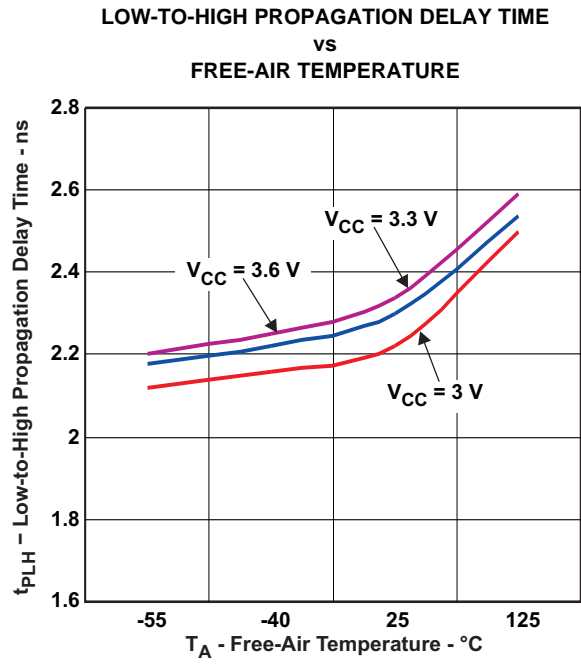


Figure 6.

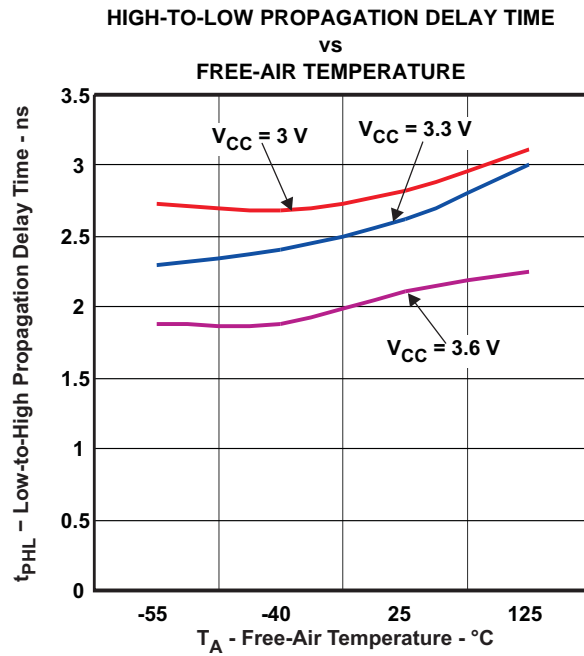
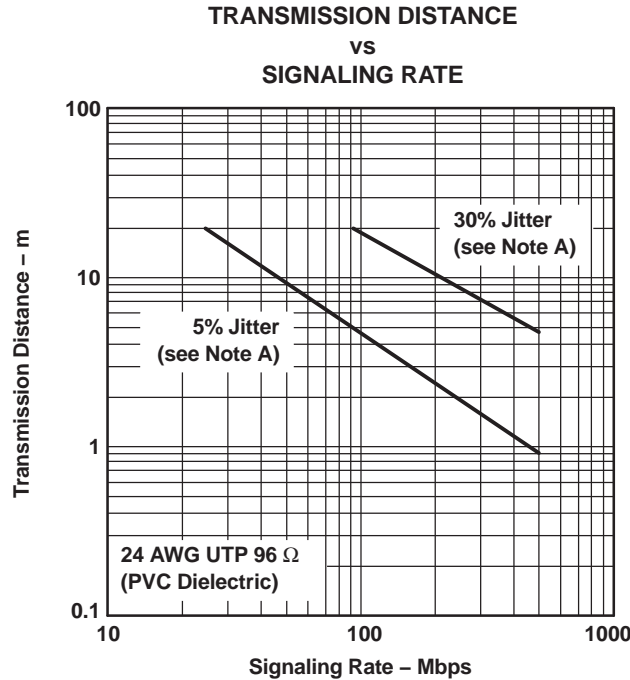


Figure 7.

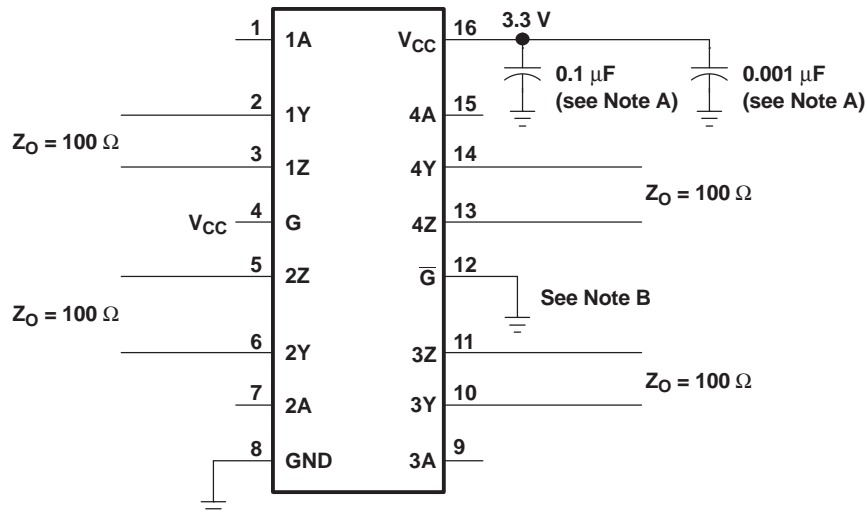
APPLICATION INFORMATION

The SN65LVDS31 is generally used as a building block for high-speed point-to-point data transmission where ground differences are less than 1 V. The SN65LVDS31 can interoperate with RS-422, PECL, and IEEE-P1596. Drivers/receivers approach ECL speeds without the power and dual supply requirements.



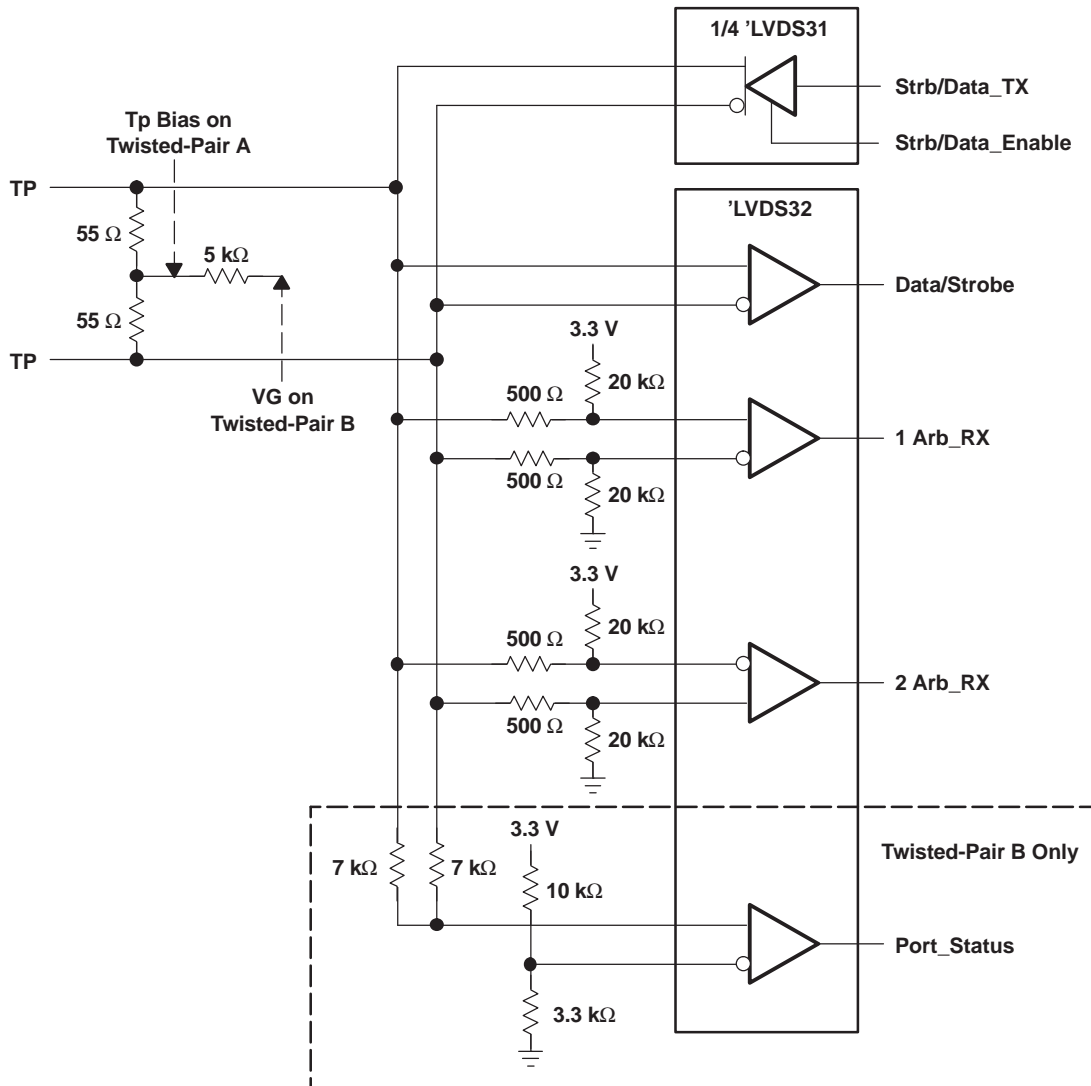
A. This parameter is the percentage of distortion of the unit interval (UI) with a pseudorandom data pattern.

Figure 8. Typical Transmission Distance Versus Signaling Rate



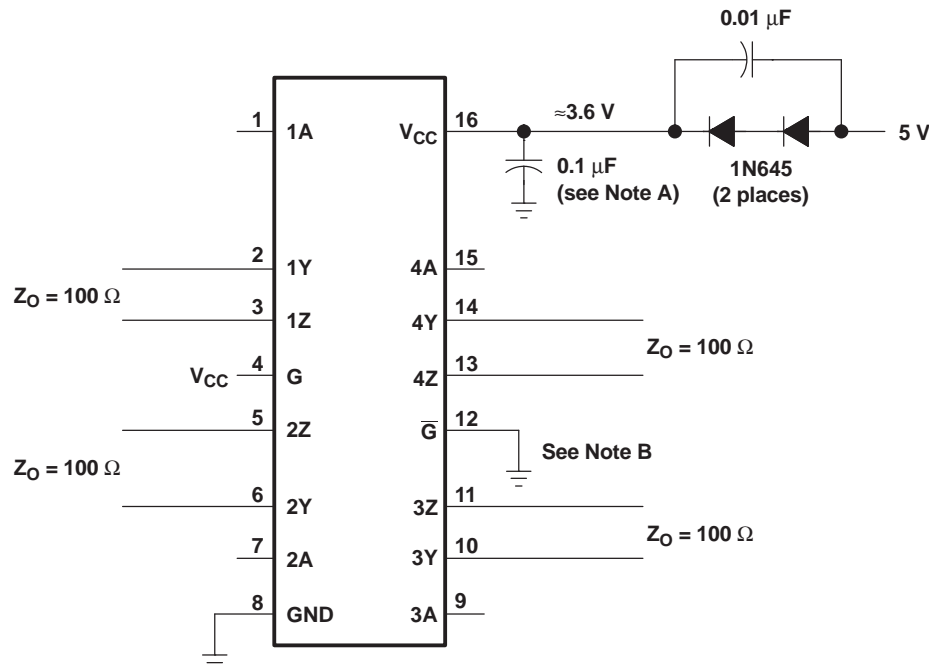
- NOTES: A. Place a 0.1-μF and a 0.001-μF Z5U ceramic, mica, or polystyrene dielectric, 0805 size, chip capacitor between V_{CC} and the ground plane. The capacitors should be located as close as possible to the device terminals.
 B. Unused enable inputs should be tied to V_{CC} or GND, as appropriate.

Figure 9. Typical Application Circuit Schematic



- NOTES: A. Resistors are leadless, thick film (0603), 5% tolerance.
 B. Decoupling capacitance is not shown, but recommended.
 C. V_{CC} is 3 V to 3.6 V.
 D. The differential output voltage of the 'LVDS31 can exceed that specified by IEEE1394.

Figure 10. 100-Mbps IEEE 1394 Transceiver



- A. Place a 0.1- μF Z5U ceramic, mica, or polystyrene dielectric, 0805 size, chip capacitor between V_{CC} and the ground plane. The capacitor should be located as close as possible to the device terminals.
- B. Unused enable inputs should be tied to V_{CC} or GND, as appropriate.

Figure 11. Operation With 5-V Supply

COLD SPARING

Systems using cold sparing have a redundant device electrically connected without power supplied. To support this configuration, the spare must present a high-input impedance to the system so that it does not draw appreciable power. In cold sparing, voltage may be applied to an I/O before and during power up of a device. When the device is powered off, V_{CC} must be clamped to ground and the I/O voltages applied must be within the specified recommended operating conditions.

RELATED INFORMATION

IBIS modeling is available for this device. Contact the local TI sales office or the TI Web site at www.ti.com for more information.

For more application guidelines, see the following documents:

- *Low-Voltage Differential Signaling Design Notes* ([SLLA014](#))
- *Interface Circuits for TIA/EIA-644 (LVDS)* ([SLLA038](#))
- *Reducing EMI With LVDS* ([SLLA030](#))
- *Slew Rate Control of LVDS Circuits* ([SLLA034](#))
- *Using an LVDS Receiver With RS-422 Data* ([SLLA031](#))
- *Evaluating the LVDS EVM* ([SLLA033](#))

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
SN65LVDS31MDREP	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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OTHER QUALIFIED VERSIONS OF SN65LVDS31-EP :

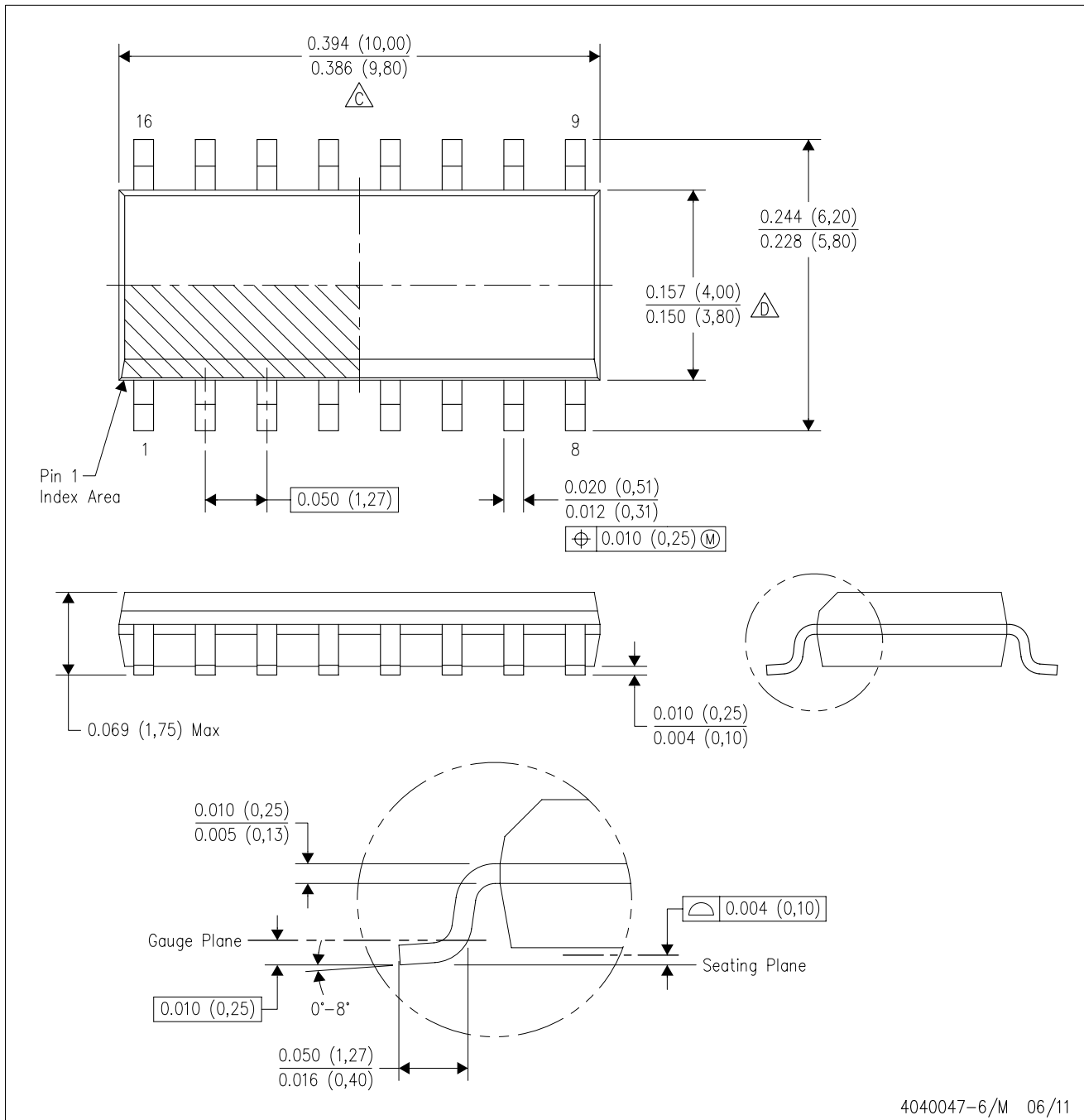
- Catalog: [SN65LVDS31](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

D (R-PDSO-G16)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
 - Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
 - E. Reference JEDEC MS-012 variation AC.

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